

AMENDMENTS TO THE SPECIFICATION

Please replace the first full paragraph on page 4 with the following:

Based on the subsequent development of techniques, it has been found that a reliable hetero junction can be formed without unfavorably inducing a decrease in crystallinity such as producing a dislocation even when a material with lattice misfit is used provided that the misfit is within a limit of elastic deformation, so that there has been made an attempt to practically use an epitaxial substrate which utilizes $\text{In}_x\text{Ga}_{(1-x)}\text{As}$ as a hetero junction material. Such limit values in the lattice misfit material are given as a function of composition and layer thickness, and in a material based on a InGaAs layer with respect to a GaAs layer for example, the limit value has theoretically been known to be represented by an equation as described in J. Crystal Growth, 27 (1974) p.118 and in J. Crystal Growth, 32 (1974)(1976) p.265, and this theoretical equation is known to be experimentally correct as a whole.